PCN Num	ber:	201	405050	001					PCN Da	te:	05/16/2014	
Title:	itle: Qualification of Additional Fab (DMOS6), Assembly/Test (TAI) and Cu Wire Option fo select MSP430FR57xx devices in the TSSOP Package						ire Option for					
Customer	r Contact:	PCN /	Manager		Phone	e: +1(2	14)480-603	7	Dept:	Qu	ality Services	
*Proposed 1 st Ship Dat		te:	08/16/20		Estim		ted Sample		Date Provided at Sample request		ovided at	
Change T	ype:								-		•	
Assembly Site			Desig			<u>jn</u>	IN			Wafer Bump Site		
Asse	embly Process	Data Sheet			Wafer Bump Material							
	Assembly Materials			Part number ch			change		Wafer Bump Process			
Mechanical Specificatio			X Test Site				\square					
Packing/Shipping/Labeling				Test	st Process 📃 Wafer				Materials			
									Wafei	· Fab	Process	
					PCN	Deta	ls					
Description	on of Change	:										
	b Differences Qualified Site		ocess, v	wafe	er dia.	Additi	onal Site, pr	oce	ss, wafe	er dia		
DP1DM5,	E035 Process, 2	00mm	I			DMOS	6, E035 Proc	ess	, 300m	n		
	v Site Materia		ferenc	es f	or DA	Packad	e (There a	-0 n	o otho	r BO	M changes)	
Material		Cur	rent Sit				Additional	Site	/TAI			
	Diameter	Cur 0.96	rent Sit				Additional 0.8 mil	Site	/TAI			
		0.96	rent Sit				Additional	Site	/TAI			
Bond Wire Mold Com Assembly Material	pound / Site Materia	0.96 4209	r ent Sit 5 mil 9002	es f	ILA or PW		Additional 0.8 mil 4211471	Site	o othe			
Bond Wire Mold Com Assembly Material	pound	0.96 4209	rent Sit	es f	ILA or PW		Additional 0.8 mil 4211471 ge (There a	Site	o othe			
Bond Wire Mold Com Assembly Material Bond Wire	pound / Site Materia	0.96 4209 I Diff Curr Au 0.96	rent Sit	es f	ILA or PW		Additional 0.8 mil 4211471 ge (There a Additional	Site	o othe			
Bond Wire Mold Com Assembly Material Bond Wire	pound / Site Materia • Composition • Diameter	0.96 4209 I Diff Curr Au 0.96	rent Sit 5 mil 9002 ferenc rent Sit	es f	ILA or PW		Additional 0.8 mil 4211471 ge (There a Additional Cu	Site	o othe			
Bond Wire Mold Com Material Bond Wire Bond Wire Mold Com Device Gr Group 1 I • 38 Group 2 I • 28	pound Site Materia Composition Diameter pound rouping (show Devices: pin DA packag Devices: pin PW packag	0.96 4209 1 Diff Cur Au 0.96 4200 wn ir ie/On ge/Ad	rent Sit	es f te/M uct / ng F	ILA or PW ILA Affecto Tab site te, A/T	Packag	Additional 0.8 mil 4211471 ge (There a Additional Cu 0.8 mil 4211471 ion)	re r Site	no othe	r BO	M changes)	
Bond Wire Mold Com Material Bond Wire Bond Wire Mold Com Device Gr Group 1 I • 38 Group 2 I • 28 Test cover test MQ.	pound Site Materia Composition Diameter pound rouping (show Devices: pin DA packag Devices: pin PW packag rage, insertions	0.96 4209 1 Diff Cur Au 0.96 4200 wn ir ie/On ge/Ad	rent Sit	es f te/M uct / ng F	ILA or PW ILA Affecto Tab site te, A/T	Packag	Additional 0.8 mil 4211471 ge (There a Additional Cu 0.8 mil 4211471 ion)	re r Site	no othe	r BO	M changes)	
Bond Wire Mold Com Material Bond Wire Bond Wire Mold Com Device Gr Group 1 I • 38 Group 2 I • 28 Test cover test MQ. Reason fo	pound Site Materia Composition Diameter pound rouping (show Devices: pin DA packag Devices: pin PW packag	0.96 4209 1 Diff Curr Au 0.96 4200 wn ir e/On ge/Ad	rent Sit	es for te/M uct / ng F ab si	ILA or PW ILA Affecto Tab site te, A/T remain	Packag	Additional 0.8 mil 4211471 ge (There a Additional Cu 0.8 mil 4211471 ion)	re r Site	no othe	r BO	M changes)	

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None Changes to product identification resulting from this PCN: There will be no change to topside symbol. Shipment Labels: **Current Fab Site** Chip site code (20L) Chip country code (21L) Chip Site DP1DM5 USA DM5 Additional Chip site code (20L) **Chip Site** Chip country code (21L) DMOS6 DM6 **USA** Note: The die revision code will change from "H" (DP1DM5) to "J" (DMOS6). This is only for tracking purposes. There is no change to the die. **Current Assembly Site** Assembly Site Assembly site Origin (22L) Assembly country Origin (23L) **TI-Malavsia** MLA MYS Additional Assembly country Origin (23L) Assembly site Origin (22L) **Assembly Site** TWN TAI Taiwan Device Marking for TI Malaysia and TI Taiwan are the same. Assembly site code for TI Malaysia = KAssembly site code for TI Taiwan = T Sample product shipping label (not actual product label) TEXAS INSTRUMENTS (Pb) (1P) SN74LS07NSR G4 MADE IN: Malaysia 2DC: 2Q: (a) 2000 (D) 0336 31T)LOT: 3959047MLA 4W) TKY(1T) 7523483S12 MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: (2P) REV: 0033317 CC0:USA (L)T0:1750 (V) (21L) (20L) CSO: SHE (22L) ASO: MLA LBL: 5A (23L) ACO: MYS

Product Affected:						
Group 1: 38 pin DA package devices/Only adding Fab site						
MSP430FR5721IDA	MSP430FR5725IDAR	MSP430FR5731IDA	MSP430FR5735IDAR			
MSP430FR5721IDAR	MSP430FR5727IDA	MSP430FR5731IDAR	MSP430FR5737IDA			
MSP430FR5723IDA	MSP430FR5727IDAR	MSP430FR5733IDA	MSP430FR5737IDAR			
MSP430FR5723IDAR	MSP430FR5729IDA	MSP430FR5733IDAR	MSP430FR5739IDA			
MSP430FR5725IDA	MSP430FR5729IDAR	MSP430FR5735IDA	MSP430FR5739IDAR			
Group 2: 28 pin PW package devices/Adding Fab site, A/T site, and includes Cu wire change						
MSP430FR5720IPW	MSP430FR5724IPWR	MSP430FR5730IPW	MSP430FR5734IPWR			
MSP430FR5720IPWR	MSP430FR5726IPW	MSP430FR5730IPWR	MSP430FR5736IPW			
MSP430FR5722IPW	MSP430FR5726IPWR	MSP430FR5732IPW	MSP430FR5736IPWR			
MSP430FR5722IPWR	MSP430FR5728IPW	MSP430FR5732IPWR	MSP430FR5738IPW			
MSP430FR5724IPW	MSP430FR5728IPWR	MSP430FR5734IPW	MSP430FR5738IPWR			

Qualification Report MSP430FR5739IDA/PW transfer to DM6 / TAI Approved04/23/2014

Product Attributes

Attributes	Qual Device: MSP430FR5739IRHA E035.1 Process Qual	Qual Device: MSP430FR5739IDA Package Qual	Qual Device: MSP430FR5738IPW Package Qual	Supporting QBS: MSP430L092SPWR Package Qual
Assembly Site	TI-Clark	TI-TAIWAN	TI-TAIWAN	TI-TAIWAN
Package Family	QFN	TSSOP	TSSOP	TSSOP
Bond Wire Diameter (mils)	0.8	0.8	0.8	0.8
Mold Compound	4208625	4211471	4211471	4206193
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	TI-DMOS6	TI-DMOS6	TI-DMOS6	TI-DMOS5
Wafer Fab Process	E035.1	E035.1	E035.1	C035

- QBS: Qual By Similarity

- Qual Device for package MSP430FR5739IDA is qualified at LEVEL2-260CG

Qualification Results

Test Name	Condition/ Duration	Qual Device: MSP430FR5739IRHA Process Qual	Qual Device: MSP430FR5739IDA Package Qual	Qual Device: MSP430FR5738IPW Package Qual	Supporting QBS: MSP430L092SPWR Package Qual
Biased HAST	96 hrs/85%RH, 130C	-	-		3/231/0
Autoclave	96 hrs/121C / 100%	-	3/231/0		3/231/0
Temperature Cycle	500 cycles -65C/+150C	-	3/231/0		3/231/0
High Temp Storage Bake	1000hrs/150C	-	3/231/0		3/231/0
** Life Test	125C (1000 hrs)	3/231/0	-		-
	25C, 1e^7 cycles, full size	3/231/0	-		-
** FRAM data retention and imprint	125C/85C (1000 hrs)***	3/231/0	-		-
ESD CDM	500V	3/9/0	3/9/0	3/9/0	-
ESD HBM	2000V	3/9/0	3/9/0		-
Latch-Up	100mA/85C, 1.5xVcc	3/18/0	-		-

Data Displayed as: Number of lots / Total sample size / Total failed

- Preconditioning was performed for Autoclave, Biased HAST, Temperature Cycle, High Temp Storage Bake. MSL2 for MSP430FR5739IDA and MSL1 for MSP430L092SPWR are applied.

: Preconditioning: MSL 3 @ 260 *: SS data retention at 125C, OS imprint at 85CQuality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
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